

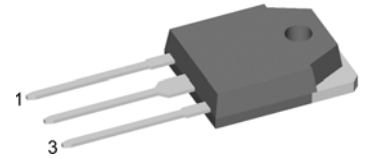
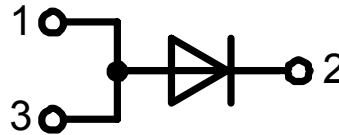
HiPerFRED²

High Performance Fast Recovery Diode
 Low Loss and Soft Recovery
 Single Diode

$V_{RRM} = 400\text{ V}$
 $I_{FAV} = 60\text{ A}$
 $t_{rr} = 45\text{ ns}$

Part number (Marking on product)

DPG 60 IM 400QB



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{RM} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{RM} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package:

- TO-3P
- Industry standard outline - compatible with TO-247
 - Epoxy meets UL 94V-0
 - RoHS compliant

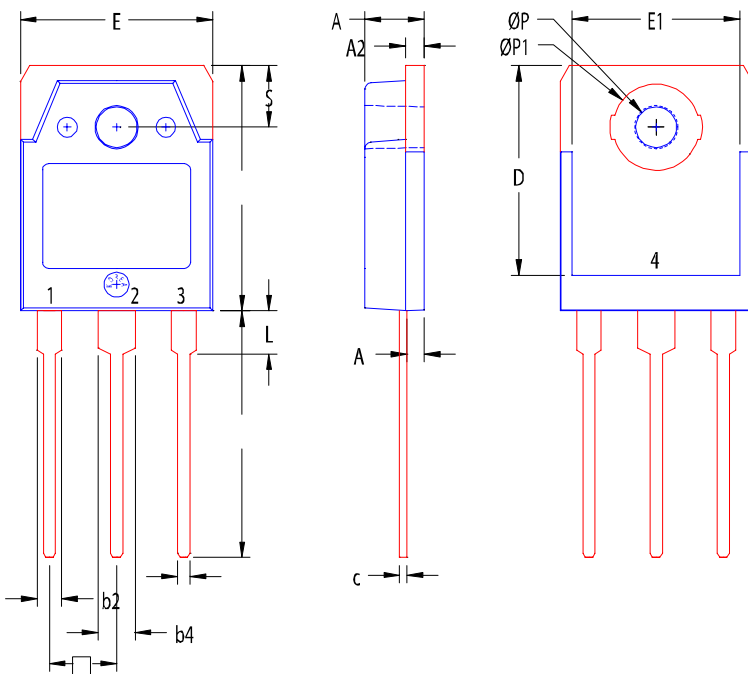
Ratings

Symbol	Definition	Conditions	Ratings			Unit	
			min.	typ.	max.		
V_{RRM}	max. repetitive reverse voltage	$T_{VJ} = 25\text{ °C}$			400	V	
I_R	reverse current	$V_R = 400\text{ V}$			1	μA	
		$V_R = 400\text{ V}$			0.3	mA	
V_F	forward voltage	$I_F = 60\text{ A}$			1.47	V	
		$I_F = 120\text{ A}$			1.80	V	
		$I_F = 60\text{ A}$	$T_{VJ} = 150\text{ °C}$			1.22	V
		$I_F = 120\text{ A}$	$T_{VJ} = 150\text{ °C}$			1.59	V
I_{FAV}	average forward current	rectangular, $d = 0.5$			60	A	
V_{FO}	threshold voltage	} for power loss calculation only			0.81	V	
r_F	slope resistance				6.1	m Ω	
R_{thJC}	thermal resistance junction to case				0.55	K/W	
T_{VJ}	virtual junction temperature		-55		175	$^{\circ}\text{C}$	
P_{tot}	total power dissipation	$T_C = 25\text{ °C}$			275	W	
I_{FSM}	max. forward surge current	$t_p = 10\text{ ms}$ (50 Hz), sine			600	A	
I_{RM}	max. reverse recovery current	$I_F = 60\text{ A};$		4		A	
		$-di_F/dt = 200\text{ A}/\mu\text{s}$	$T_{VJ} = 125\text{ °C}$			A	
t_{rr}	reverse recovery time	$V_R = 100\text{ V}$		45		ns	
			$T_{VJ} = 125\text{ °C}$			ns	
C_J	junction capacitance	$V_R = 200\text{ V}; f = 1\text{ MHz}$		60		pF	
E_{AS}	non-repetitive avalanche energy	$I_{AS} = 9\text{ A}; L = 100\text{ }\mu\text{H}$			0.5	mJ	
I_{AR}	repetitive avalanche current	$V_A = 1.5 \cdot V_R$ typ.; $f = 10\text{ kHz}$			0.9	A	

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	Unit
I_{RMS}	RMS current	per pin*			70	A
R_{thCH}	thermal resistance case to heatsink			0.25		K/W
M_D	mounting torque		0.8		1.2	Nm
F_C	mounting force with clip		20		120	N
T_{stg}	storage temperature		-55		150	°C
Weight				5		g

* I_{rms} is typically limited by: 1. pin-to-chip resistance; or by 2. current capability of the chip.

In case of 1, a common cathode/anode configuration and a non-isolated backside, the whole current capability can be used by connecting the backside.

Outlines TO-3P


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.193	4.70	4.90
A1	.051	.059	1.30	1.50
A2	.057	.065	1.45	1.65
b	.035	.045	0.90	1.15
b2	.075	.087	1.90	2.20
b4	.114	.126	2.90	3.20
c	.022	.031	0.55	0.80
D	.780	.791	19.80	20.10
D1	.665	.677	16.90	17.20
E	.610	.622	15.50	15.80
E1	.531	.539	13.50	13.70
e	.215 BSC		5.45 BSC	
L	.779	.795	19.80	20.20
L1	.134	.142	3.40	3.60
ØP	.126	.134	3.20	3.40
ØP1	.272	.280	6.90	7.10
S	.193	.201	4.90	5.10

- 1 - GATE
- 2 - DRAIN (COLLECTOR)
- 3 - SOURCE (EMITTER)
- 4 - DRAIN (COLLECTOR)

All metal area are tin plated.